

ATTY DOCKET NO.

0039-7271-2SRD

SERIAL NO.

NEW APPLICATION

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Daisaburo TAKASHIMA, et al.

FILING DATE

HEREWITH

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
	AO				
	AP				
	AQ				
	AP				
	AS				
	AT				
	AU				
	AV				

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DD	AW	A. INANI, et al., "Performance Considerations in Using High-k Dielectrics for Deep Sub-Micron MOSFETs," 1998 International Conference on Solid State Devices and Materials, Hiroshima, (1998), Pgs. 94-95.
TD	AX	Hiroshi TAKATO, et al., "Impact of Surrounding Gate Transistor (SGT) for Ultra-High-Density LSI'S," IEEE Transactions On Electron Devices. Vol. 38, No. 3, (March 1991), Pgs. 573-578.
	AY	
	AZ	

Examiner

Date Considered

5/23/01

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.